

-	4	(plasma adj1 nitridation) and (((anneal\$3 "heat-treatment" heat\$3) with oxynitride) same (gate adj1 electrode).bi.)	USPAT; US-PGPUB	2004/09/14 09:02
-	6	((plasma adj1 nitridation) with oxynitride) same (gate adj1 electrode).bi.	USPAT; US-PGPUB	2004/09/14 09:03
-	597	((anneal\$3 "heat-treatment" heat\$3) with oxynitride) same (nitrid\$5 (plasma adj1 nitradation)).bi.	USPAT; US-PGPUB	2004/09/14 09:26
-	6	((anneal\$3 "heat-treatment" heat\$3) with oxynitride) same (nitrid\$5 (plasma adj1 nitradation)) same ((electrode gate) with aluminum).bi.	USPAT; US-PGPUB	2004/09/14 09:50
-	1	20020094593.pn. and plasma	USPAT; US-PGPUB	2004/09/14 09:51
-	1	20020094593.pn. and nitrid\$6	USPAT; US-PGPUB	2004/09/14 09:51

L Number	Hits	Search Text	DB	Time stamp
-	4	Chen-kun-hong.in.	USPAT; US-PGPUB	2004/09/14 07:29
-	859	TFT and (((pattern resist mask photoresist) with two with (portion structure geometry)) ((pattern resist mask photoresist) with (step adj1 structure))) .bi.	USPAT; US-PGPUB	2004/09/09 08:02
-	27	chou-anthony-i laibowitz-robert-benjamin.in.	USPAT; US-PGPUB	2004/09/12 09:44
-	4	(chou-anthony-i laibowitz-robert-benjamin.in.) and (SiON oxynitride)	USPAT; US-PGPUB	2004/09/12 09:49
-	114	((anneal\$3 "heat-treatment" heat\$3) with (SiON oxynitride)) same temperature same time.bi.	USPAT; US-PGPUB	2004/09/13 07:34
-	114	((anneal\$3 "heat-treatment" heat\$3) with (SiON oxynitride)) same temperature same time.bi.	USPAT; US-PGPUB	2004/09/13 07:37
-	130	(capacitor transistor) same (aluminum with (SiON oxynitride)) .bi.	USPAT; US-PGPUB	2004/09/13 07:36
-	0	((anneal\$3 "heat-treatment" heat\$3) with (SiON oxynitride)) same temperature same time.bi.) and ((capacitor transistor) same (aluminum with (SiON oxynitride)) .bi.)	USPAT; US-PGPUB	2004/09/13 07:36
-	67	(anneal\$3 "heat-treatment" heat\$3) and ((capacitor transistor) same (aluminum with (SiON oxynitride)) .bi.)	USPAT; US-PGPUB	2004/09/13 09:37
-	4173	(anneal\$3 heat\$3) with (oxygen "O.sub.2") with concentration.bi.	USPAT; US-PGPUB	2004/09/13 09:05
-	4	((anneal\$3 heat\$3) with (oxygen "O.sub.2") with concentration.bi.) and (((anneal\$3 "heat-treatment" heat\$3) with (SiON oxynitride)) same temperature same time.bi.) ((capacitor transistor) same (aluminum with (SiON oxynitride)) .bi.))	USPAT; US-PGPUB	2004/09/13 08:41
-	0	(anneal\$3 heat\$3) with (oxygen "O.sub.2") with concentration with "per billion".bi.	USPAT; US-PGPUB	2004/09/13 09:05
-	22	(anneal\$3 heat\$3) with (oxygen "O.sub.2") with concentration with "per million".bi.	USPAT; US-PGPUB	2004/09/13 09:32
-	13	(anneal\$3 heat\$3) with concentration with "per billion".bi.	USPAT; US-PGPUB	2004/09/13 09:35
-	3643	(gate (storage adj1 node) electrode) with ("SiON" oxynitride).bi.	USPAT; US-PGPUB	2004/09/13 09:37
-	491	((anneal\$3 "heat-treatment" heat\$3) with ("SiON" oxynitride)) and ((gate (storage adj1 node) electrode) with ("SiON" oxynitride).bi.)	USPAT; US-PGPUB	2004/09/13 09:38
-	4	((anneal\$3 "heat-treatment" heat\$3) with ("SiON" oxynitride)) and ((gate (storage adj1 node) electrode) with ("SiON" oxynitride).bi.)) and MIM and transistor	USPAT; US-PGPUB	2004/09/13 10:44
-	16	(Al aluminum) with ("SiON" oxynitride) with (transistor FET).bi.	USPAT; US-PGPUB	2004/09/14 08:31
-	32	(anneal\$3 "heat-treatment" heat\$3) with ("SiON" oxynitride) with (transistor FET).bi.	USPAT; US-PGPUB	2004/09/13 10:54
-	23	(Al aluminum) and ((anneal\$3 "heat-treatment" heat\$3) with ("SiON" oxynitride) with (transistor FET).bi.)	USPAT; US-PGPUB	2004/09/13 11:02
-	73	((anneal\$3 "heat-treatment" heat\$3) with oxynitride) same (gate adj1 electrode).bi.	USPAT; US-PGPUB	2004/09/14 09:12
-	55	(Al aluminum) and (((anneal\$3 "heat-treatment" heat\$3) with oxynitride) same (gate adj1 electrode).bi.)	USPAT; US-PGPUB	2004/09/14 08:53